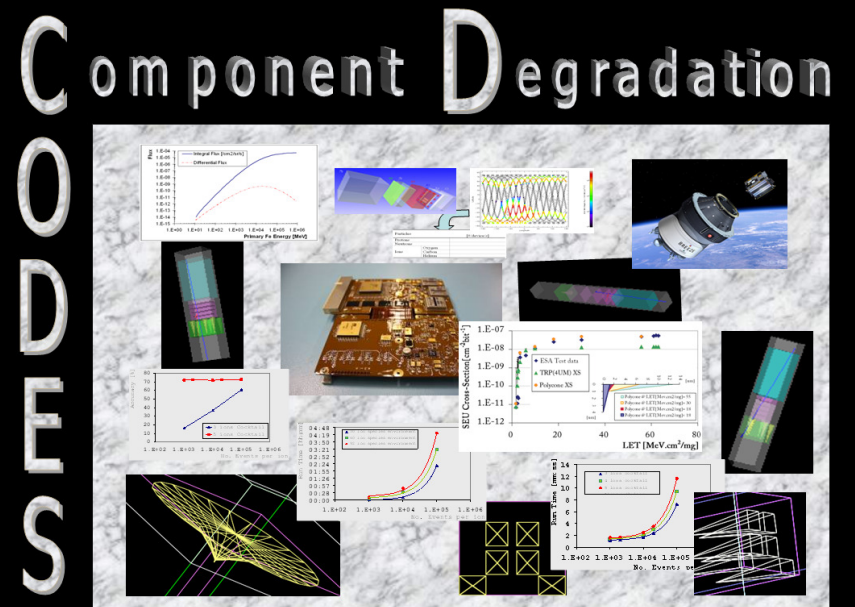


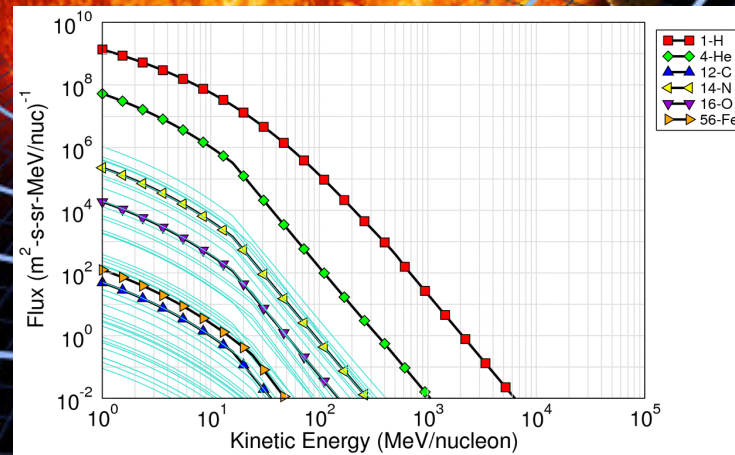
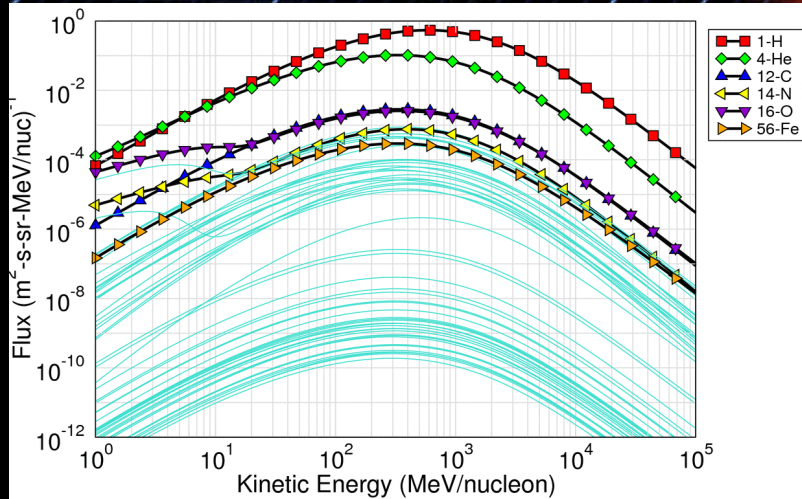
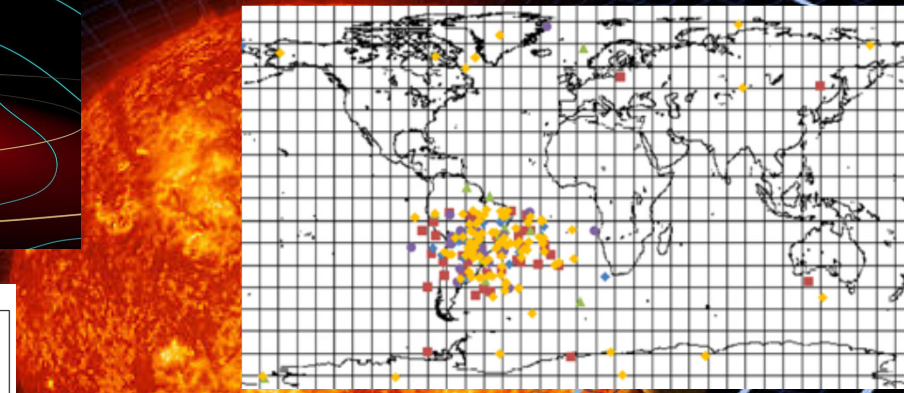
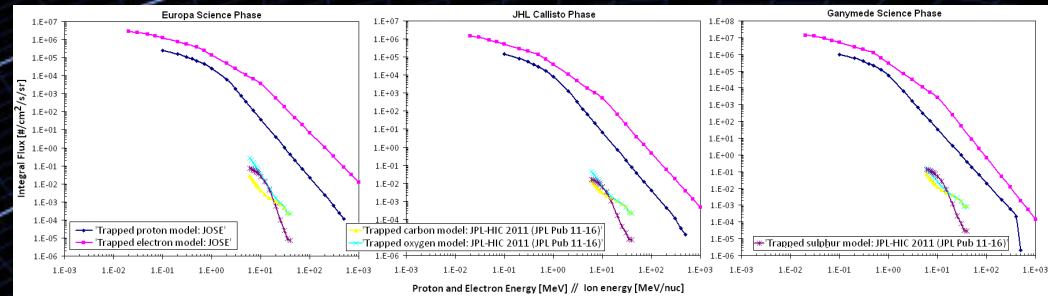
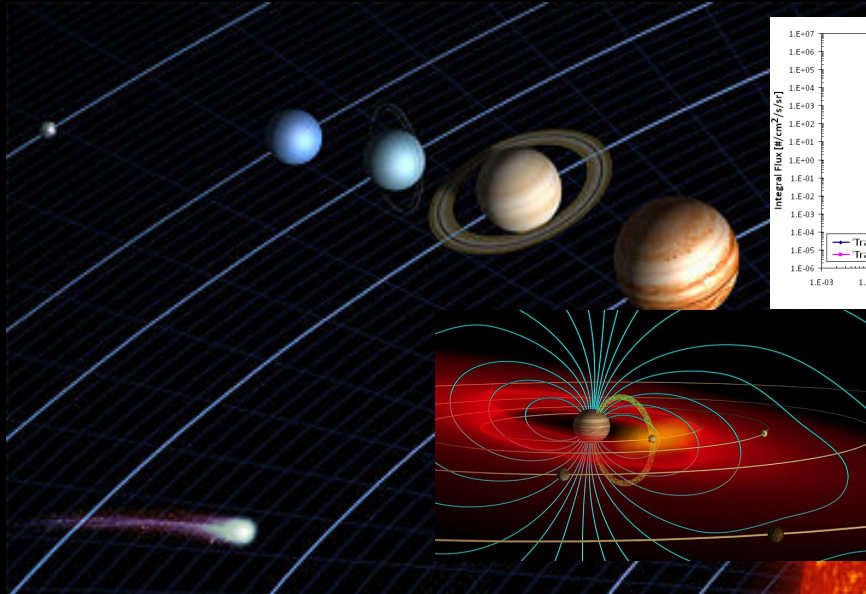
Simulation of Single Event Effects and rate prediction. CODES an ESA tool component degradation simulation tool

A. Keating, S. Joyce, A. Zadeh, M. Pimenta,
E. Daly, P. Gonçalves
ESA Project:
18121/04/NL/CH



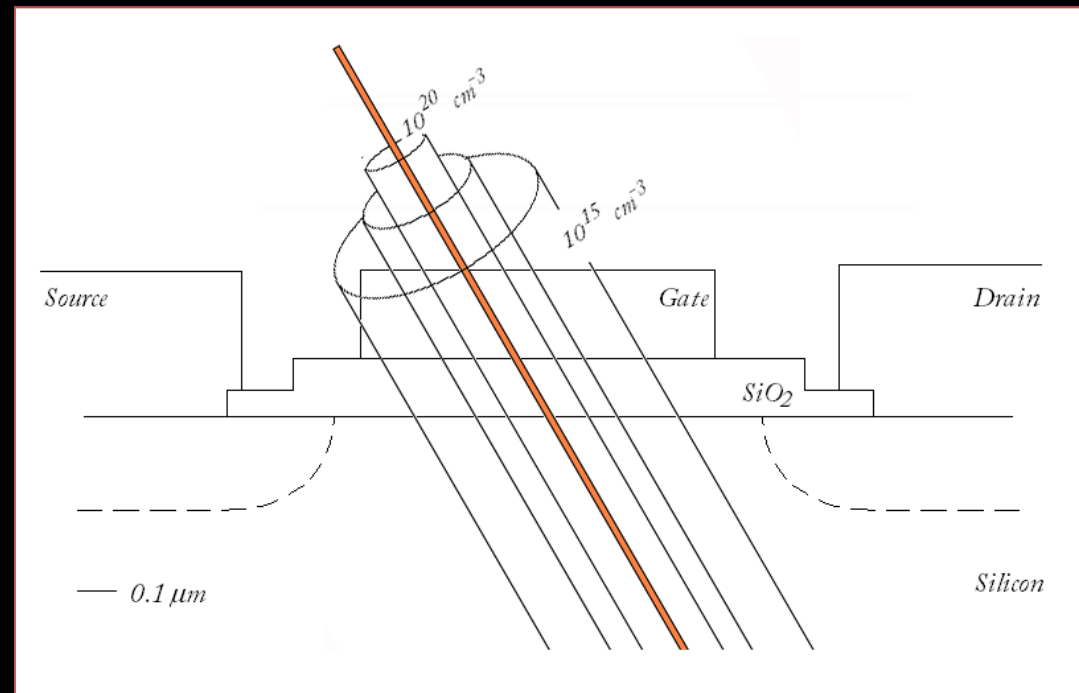
- Simulation of SEE effects
 - Environment thru shielding and processing layers
 - Energy deposition distribution at SV
- Sensitive Volume Fit (SVFIT) Module
- CODES: the top level integrated tool
- Additional Models developed to be included later
- Conclusions

Radiation Environment



Single Event Effects

- A transient phenomenon : Decaying with time
- *e-h pair generation threshold* in the target material (3.6eV Si)

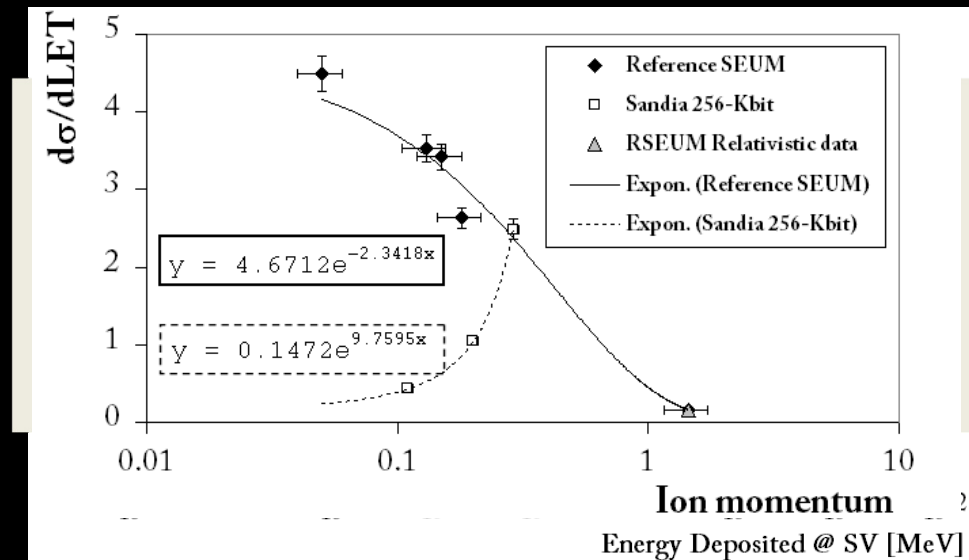


SEE Mechanisms: Stopping power and nuclear Reactions

- Keating et al. (2012). Modelling the effects of low-LET cosmic rays on electronic components, Radiat Environ Biophys, DOI 10.1007/s00411-012-0412-2.

$$\sigma_{\text{SEU}} \propto \left(\left[\int_{x=0}^{x=l} \frac{dE^a}{dx} dx \right] \cdot \sigma[X(a, b)Y] \cdot \eta_c(x) \cdot f[Z, A]^{\text{target}} \right)$$

- Stopping power
- $\sigma[X(a, b)y]$ nuclear cross section
- $\eta_c(x)$ is the charge collection yield
- Z and A



Drift & Diffusion in the semiconductor

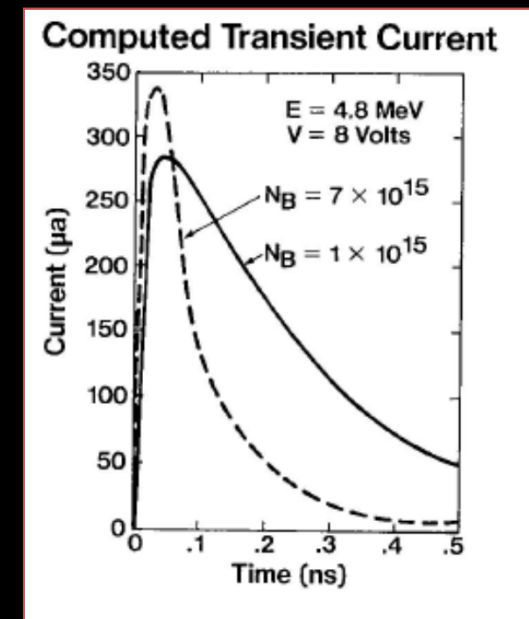
- Electron-hole pairs are separated and transported by the electric field (drift) and by diffusion

$$J_i = q n_i \mu_i E + q D_i \text{grad}(n_i);$$

$\underbrace{\hspace{10em}}_{\text{drift}} \quad \underbrace{\hspace{10em}}_{\text{diffusion}}$

$i=e,h$

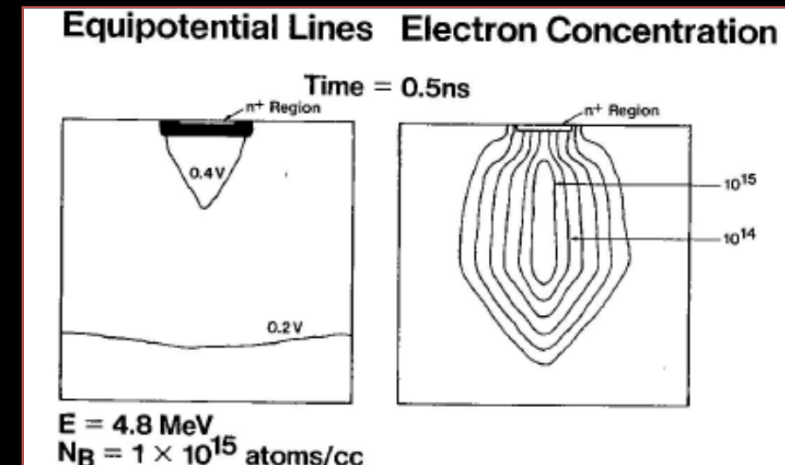
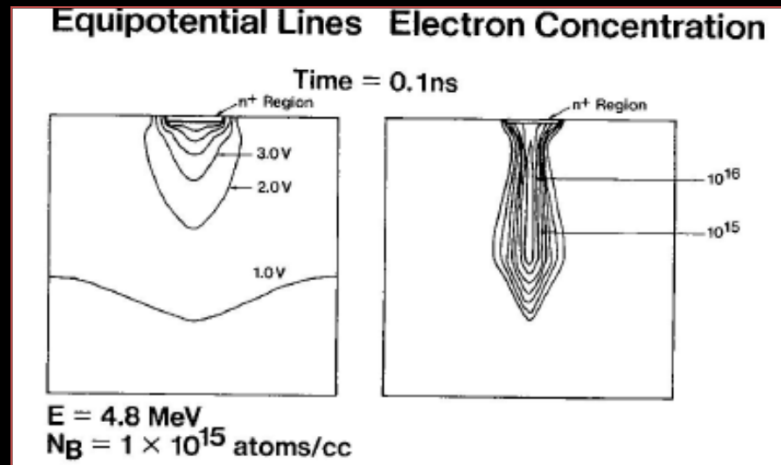
- Drift: $t \sim 0.5 \text{ ns}$ $d < 10 \mu\text{m}$
- Diffusion: $t > 0.5 \text{ ns}$ $d > 10 \mu\text{m}$
- Part may recombine (function of injection level, Ma 1989)
- Charges collected by electrodes may propagate thru the circuit: *Transient "ionocurrent"*



Drift & Funnelling

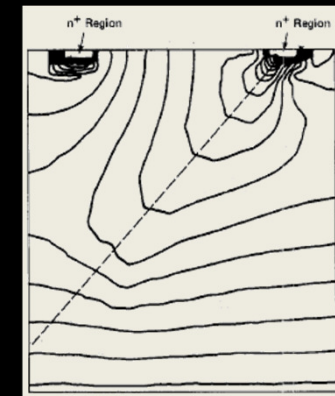
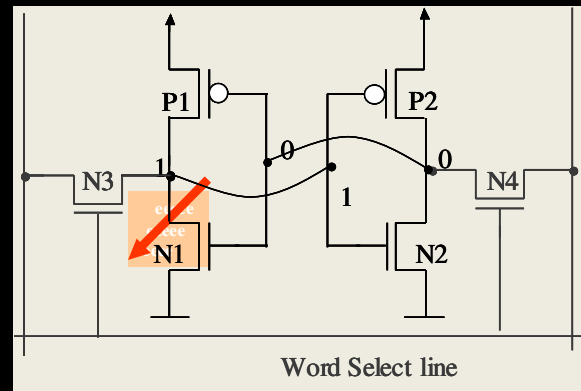
C. M. Hsieh, P. C. Murley, 1981

- Drift charge : prompt charge collection ($\sim 0.5\text{ns}$)
- Before the ion the *Electrical field*, E , is limited to the *depletion region*
- The ion track (or the e-h pair plasma) extends E far down into bulk Si



- The device behaviour depends on the field (ξ), Incoming particle ($\beta\gamma \sim P/M$) and on the angle of incidence (θ)

$$Q_{\text{collected}} = f(\xi, \lambda, \theta) > Q_{\text{crit}}$$

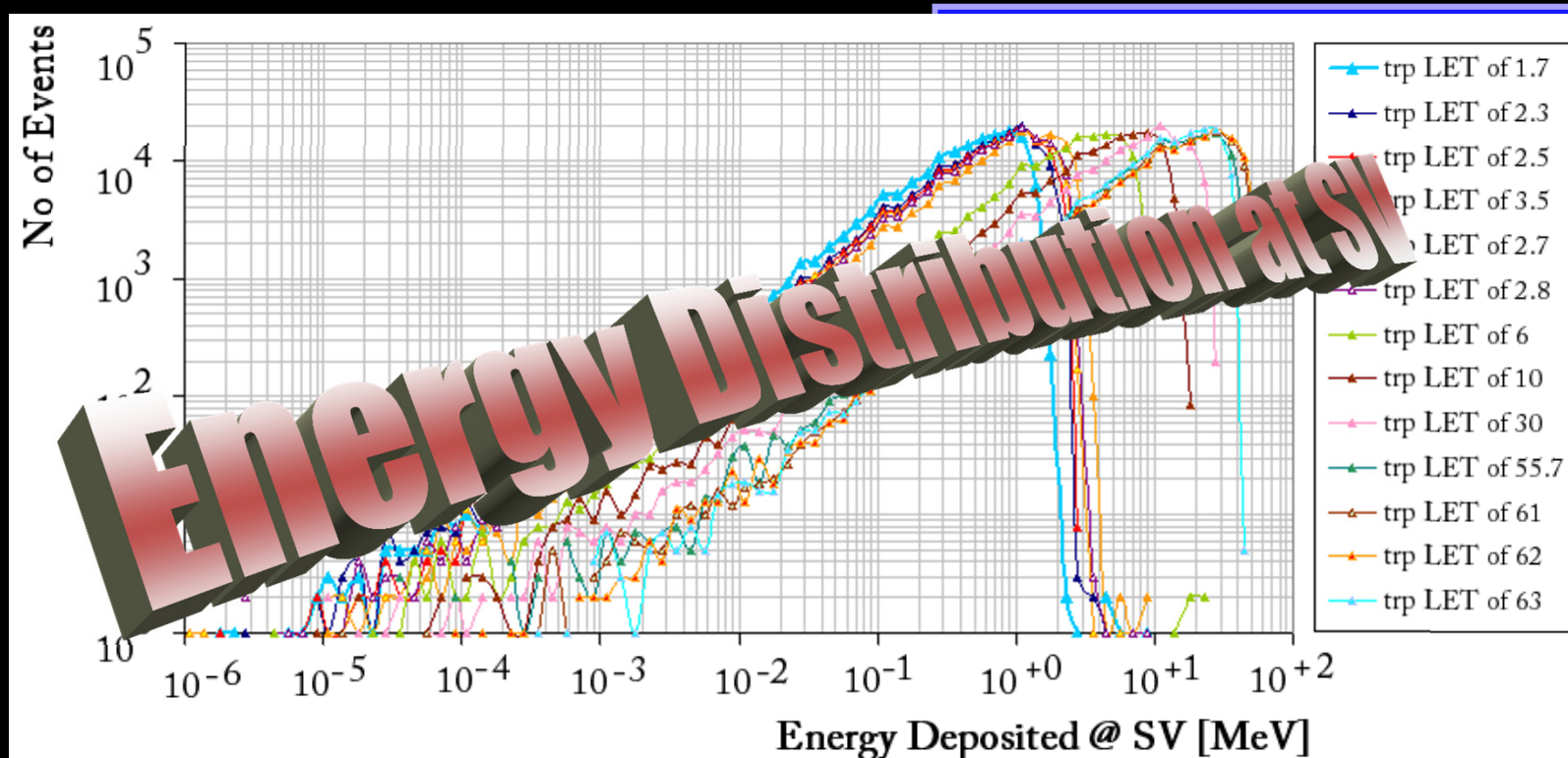


- The critical charge depends on the node capacitance, voltage and the response time of the device

$$Q_{\text{crit}} = C_{\text{node}} \cdot V_{\text{node}} + \tau_{\text{switch}} \cdot I_{\text{restore}}$$

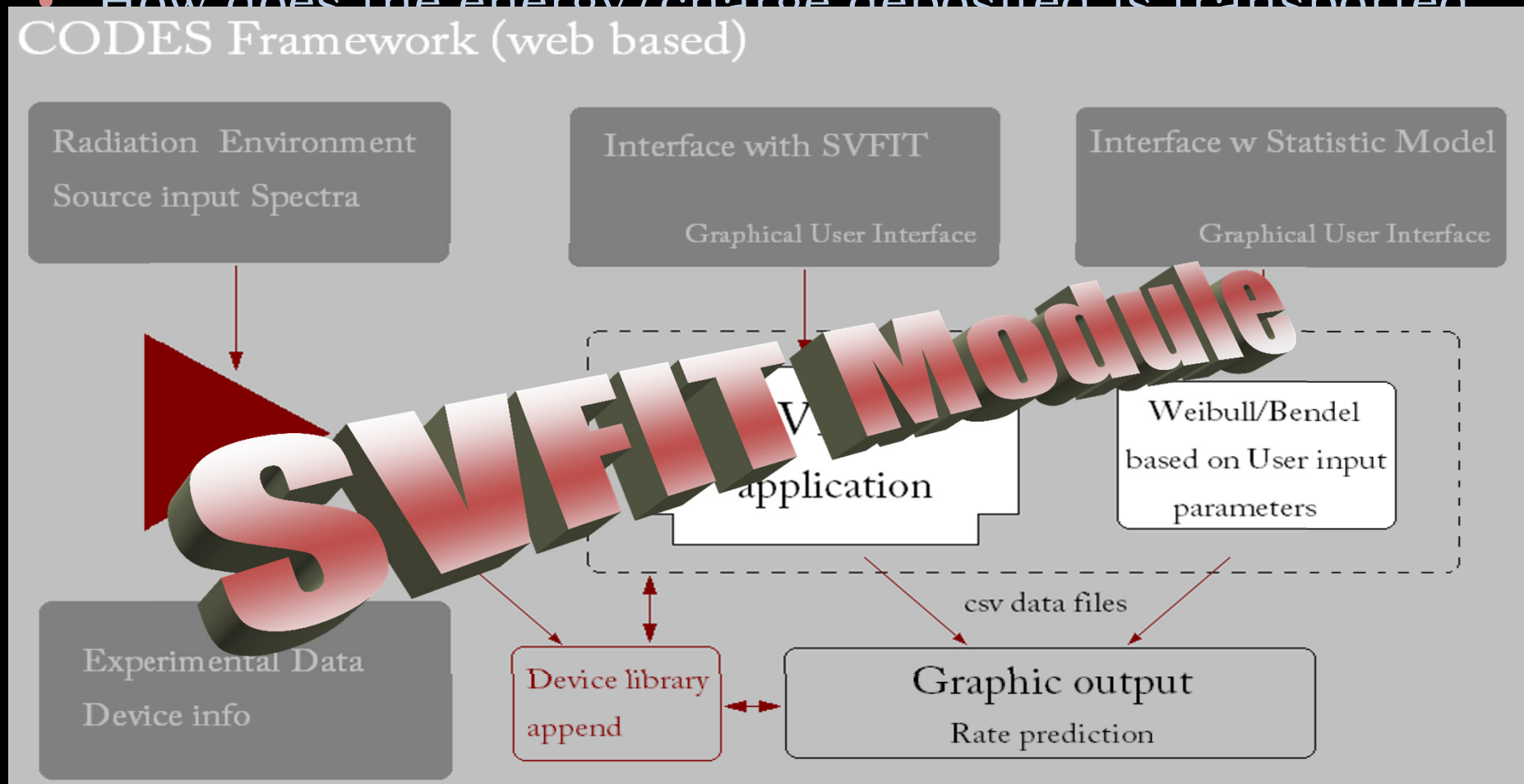
Which answers can GEANT4 Give?

- Particle physics simulation tool, for particle transport and interaction with matter used for simulating:

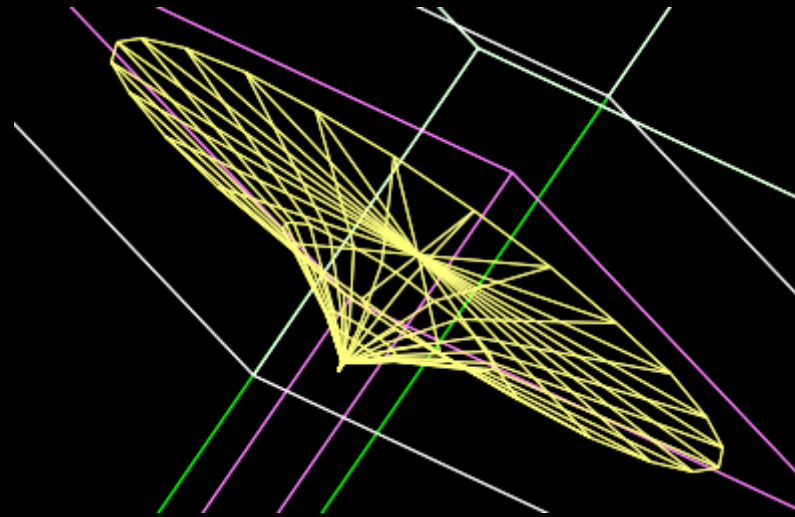


What are the remaining questions?

- How does the energy/charge deposited is transported
- CODES Framework (web based)



- Experimental data
 - Device Response function
 - Function of field effects
 - Cristal lattice effects
 - Experimental conditions



- SVFIT:
 - Fits device sensitivity to adjust experimental device response function

CODES Framework

www.cybercodes.net/framework/V1.5.9.6/WebInterface/

CODES Framework

Prediction of Single Event Effects in EEE devices

HOME SVFIT CODES HELP

SVFIT: Web Interface

Component Type:

Component Description:

Component Number:

N. of Bits[unit bit]:

Geometry: Parallelepiped "RPP"

Manufacturer:

Email:

Re-Type Email:

Select no. of Transistors / Active Regions in the memory cell: 1 2 4 6

Keep Information Private:

No. of non-active layers above SV: ?

Guideline SV Dimensions[um]: x y Depth

Depth Uncertainty Variation: 0 10% 50% 75% 90%

If Uncertainty Variation is left to 0, it is assumed that device dimensions are exact.

No file chosen

Atomic No.(Z)	Atomic Mass(A)	Charge(Q)	Ion Energy	LET	SEEXS
<input type="text" value="7"/>	<input type="text" value="15"/>	<input type="text" value="4"/>	<input type="text" value="139"/>	<input type="text" value="1.7"/>	<input type="text" value="0.00E-00"/>
<input type="text" value="10"/>	<input type="text" value="20"/>	<input type="text" value="6"/>	<input type="text" value="186"/>	<input type="text" value="3.5"/>	<input type="text" value="0.00E-00"/>
<input type="text" value="14"/>	<input type="text" value="30"/>	<input type="text" value="8"/>	<input type="text" value="278"/>	<input type="text" value="6.4"/>	<input type="text" value="0.00E-00"/>
<input type="text" value="18"/>	<input type="text" value="40"/>	<input type="text" value="12"/>	<input type="text" value="372"/>	<input type="text" value="10"/>	<input type="text" value="0.00E-00"/>
<input type="text" value="36"/>	<input type="text" value="82"/>	<input type="text" value="22"/>	<input type="text" value="768"/>	<input type="text" value="30"/>	<input type="text" value="0.00E-00"/>

No of processing events per ion:

Please use the following references when publishing results that have been produced by this site:

A. Keating, P. Goncalves, A.Zadeh, M.Pimenta, S. Coutinho, P.Broqueira, E.Daly, 2011, Validation of the component degradation simulation tool (CODES), Radiation and Its Effects on Components and Systems (RADECS), 2011 12th European Conference Proceedings, pp. 396-400, DOI 10.1109/RADECS.2011.6131414.

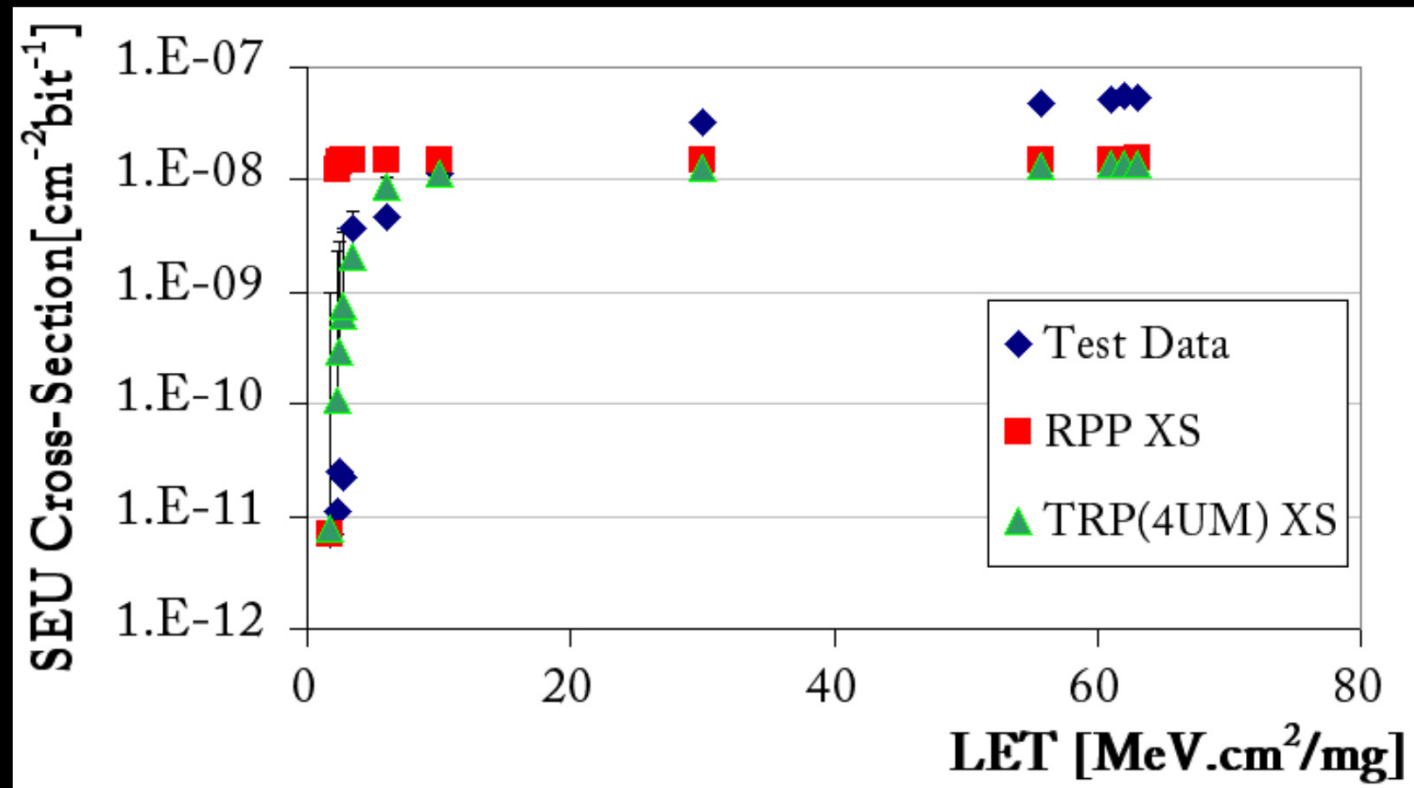
A.Keating, P. Goncalves, M.Pimenta, P.Broqueira, A.Zadeh, E.Daly, 2012 "Modeling the effects of low-LET cosmic rays on electronic components", Radiat. Environ. Biophys. Journal, DOI 10.1007/s00411-012-0412-2

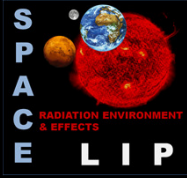
SVFIT: Web interface

- SVFIT_V. 1.5.7
- Meta Information
- SV geometry
- Email account
- Efficiency matrix: No of SV
- Library
- Non Active layers
- Guideline SV dimensions
- Depth uncertainty -> Interactive Fit
- Experimental Cocktail
- No. Events
- Credits
- Run SVFIT

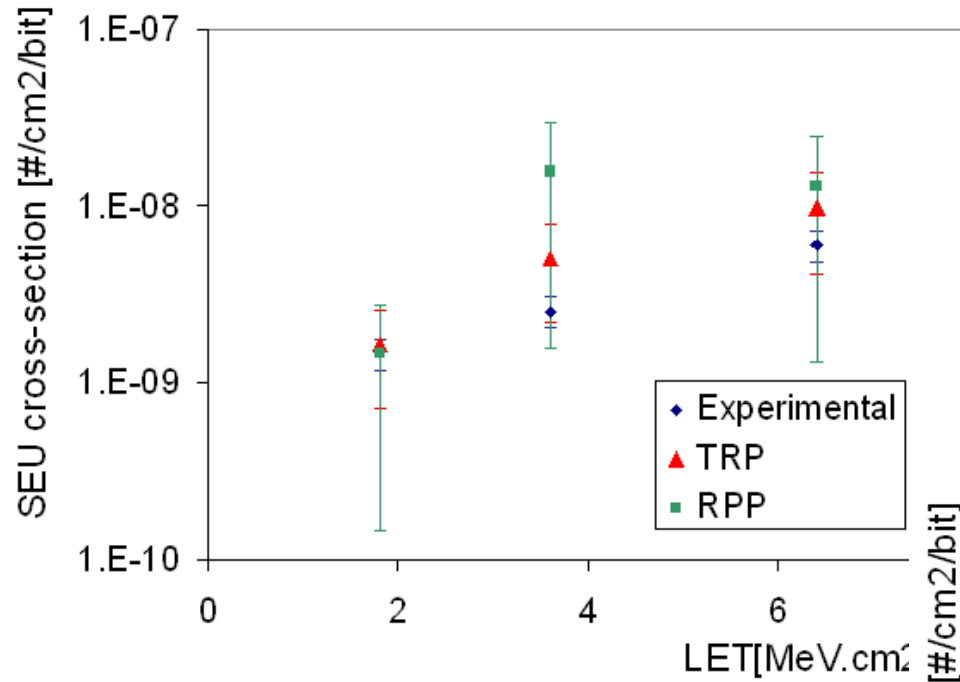
Detailed SVFIT: Published papers

- RADECS 2011
- 10^6 evts



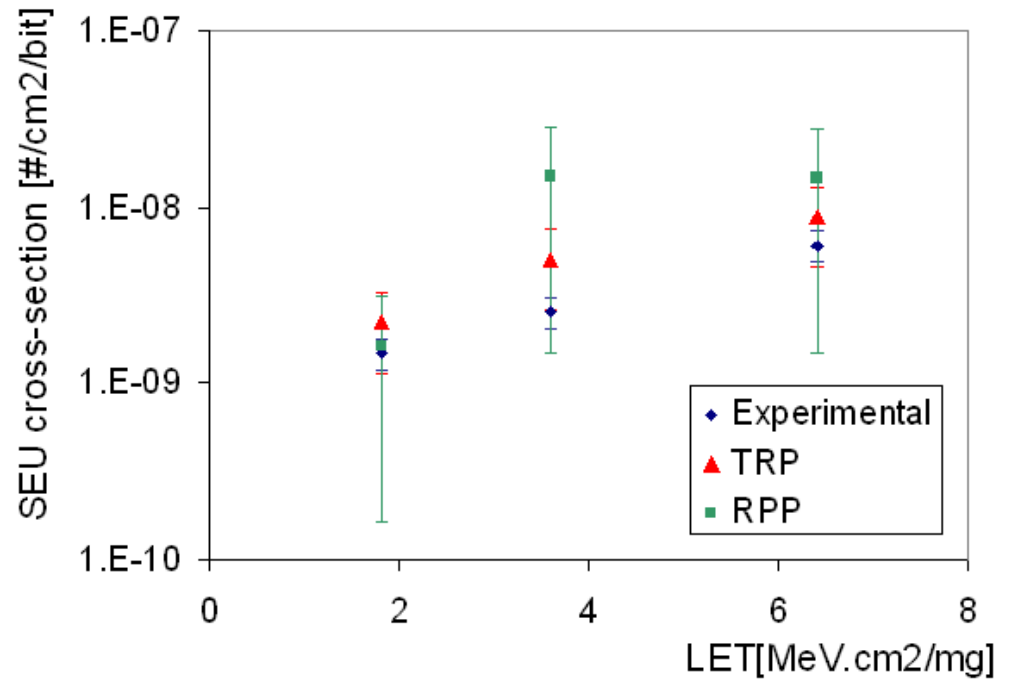


Engineering tool: ISSI1 SEU XS Reconstruction



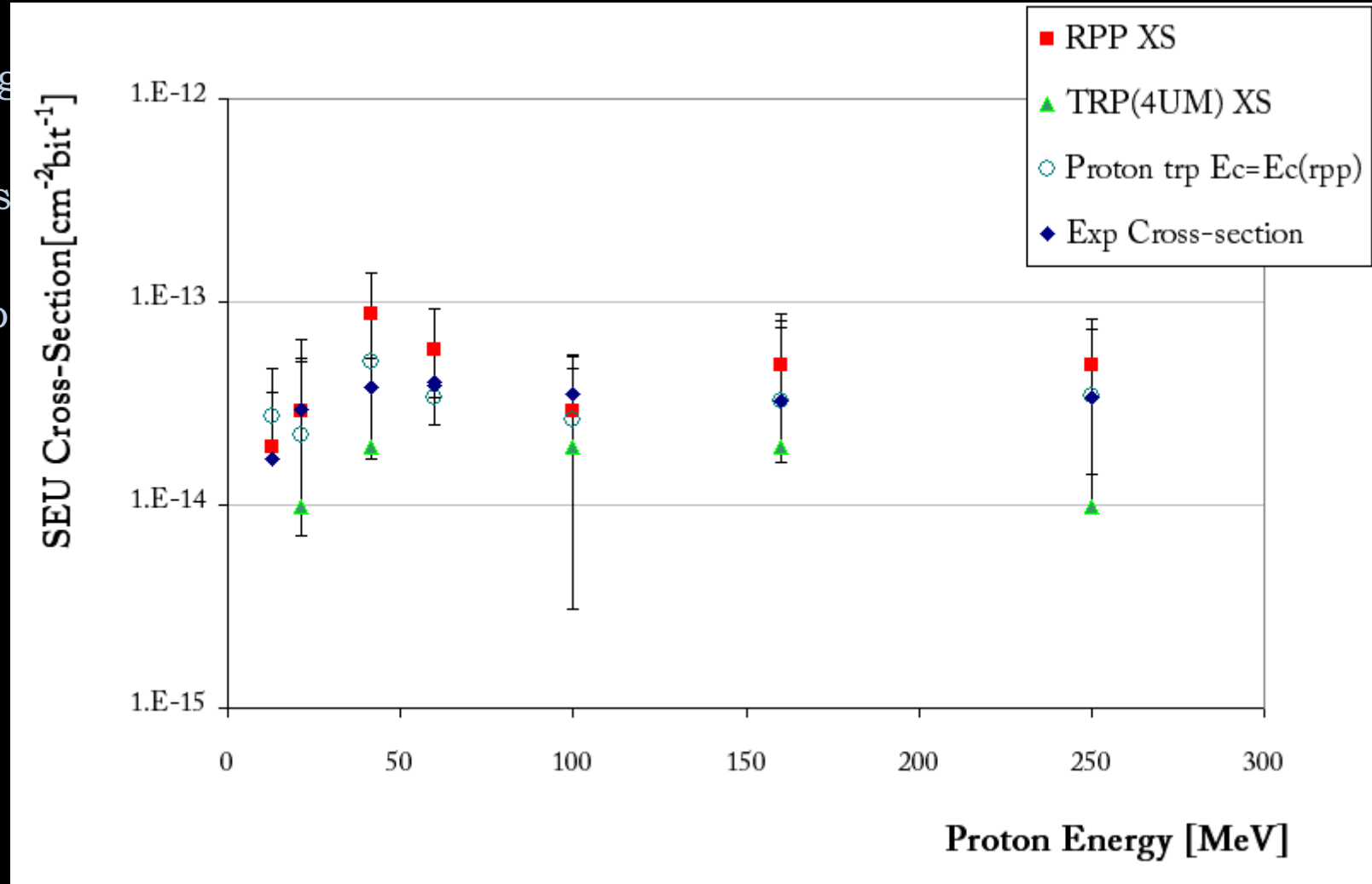
← 10³ evts

10⁶ evts →



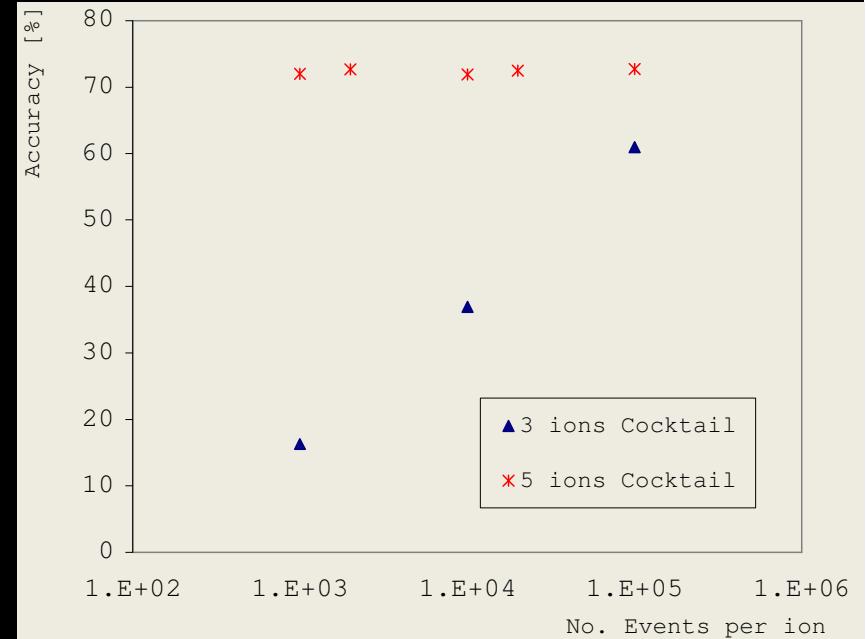
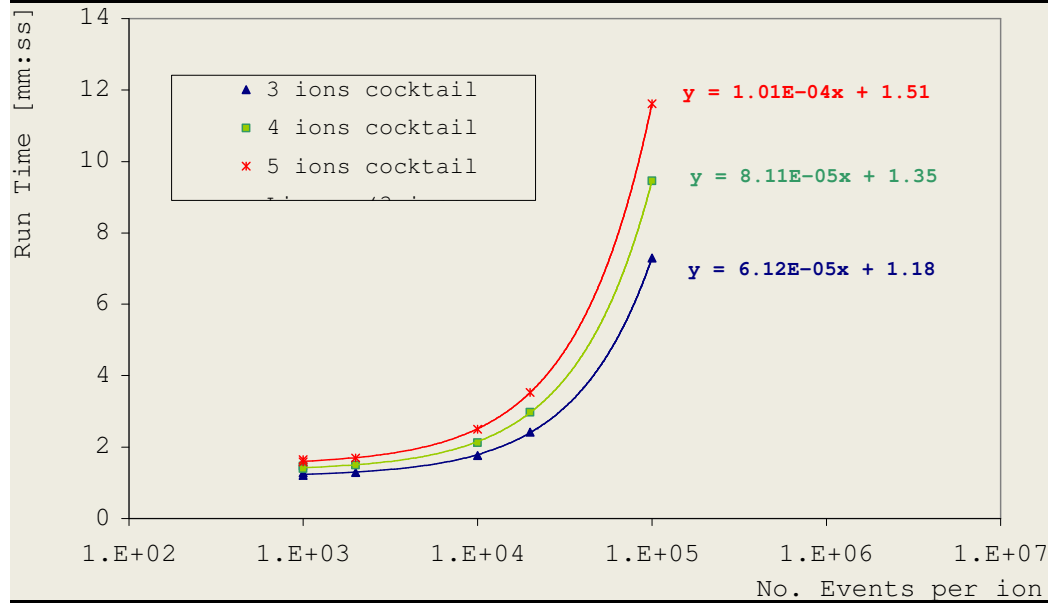
From Ion data to proton prediction

- Using
- The s
- Proto



SVFIT working for different devices

- Tests have been made for the Reference SEU Monitor and SEL monitor devices





CODES Framework

Prediction of Single Event Effects in EEE devices

[HOME](#)
[SVFIT](#)
[CODES](#)
[HELP](#)

CODES: Web Interface

Component Description

Component Type:

Component Description:

Component Number:

N. of Bits[unit bit]:

Manufacturer:

Email:

Re-Type Email:

Keep Information Private:

Geometry

Aluminium Equivalent
Shielding Layer [mm]:

Non active layers:

Sensitive volume:

No file chosen

Radiation Input

Load radiation input file:

No file chosen

Particle:

Ion specific label:

Flux Units:

Energy	Flux
1.1295E+01	3.5082E-15
1.4219E+01	5.9596E-15
1.7901E+01	1.0087E-14

Device Response function

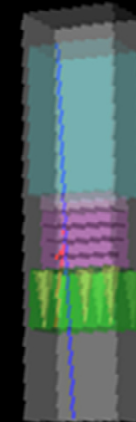
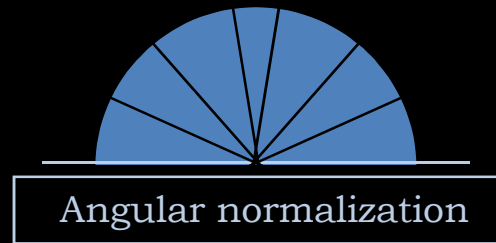
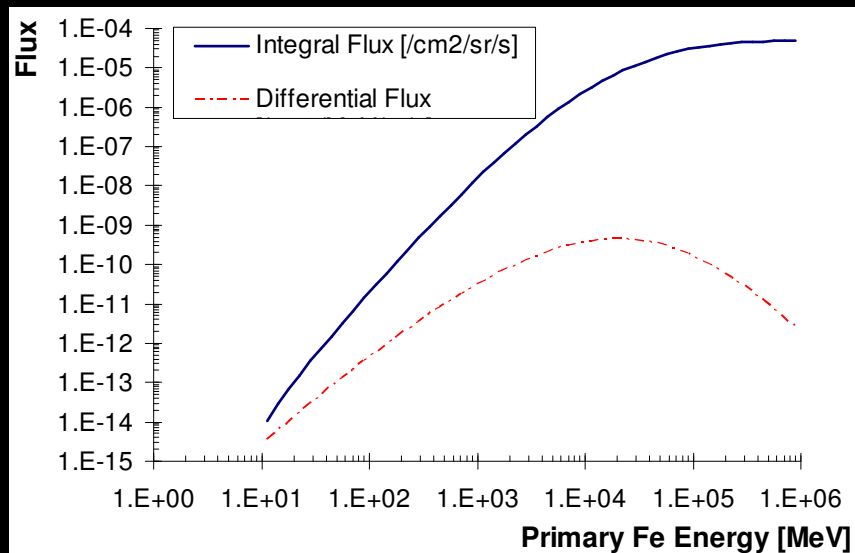
Select Method:

No file chosen

Critical Energy [MeV]:

According to the ICR

- Normalization is based on dMEREM/MARSREM normalization methods



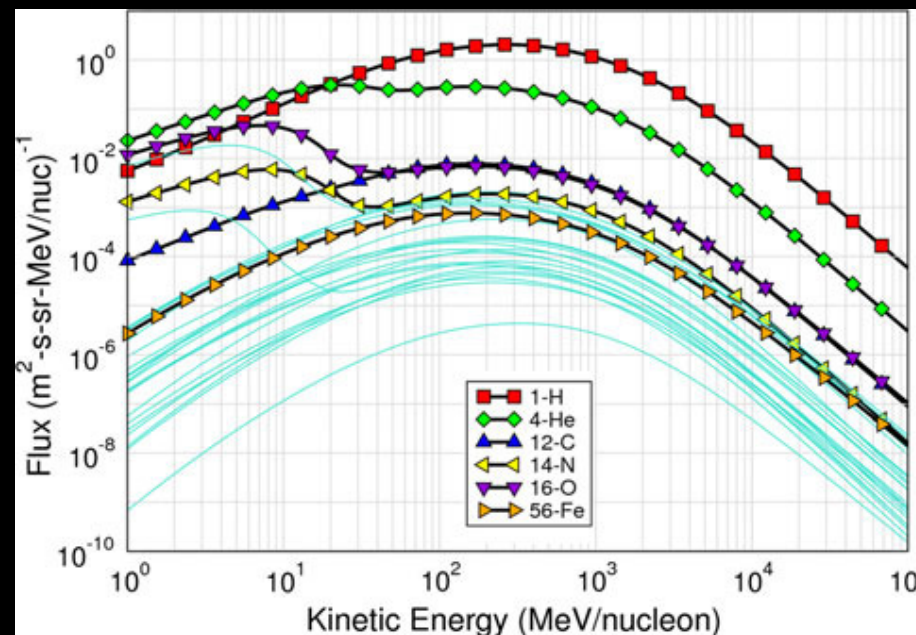
Theta Max

Primary Integral Flux Normalization

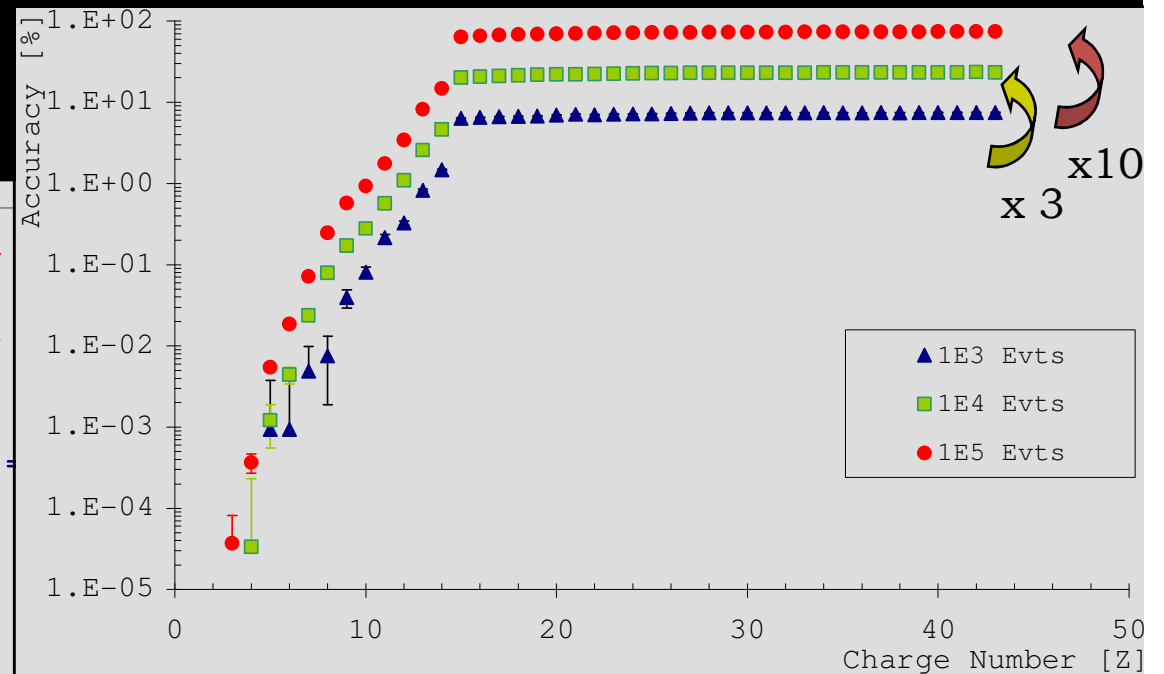
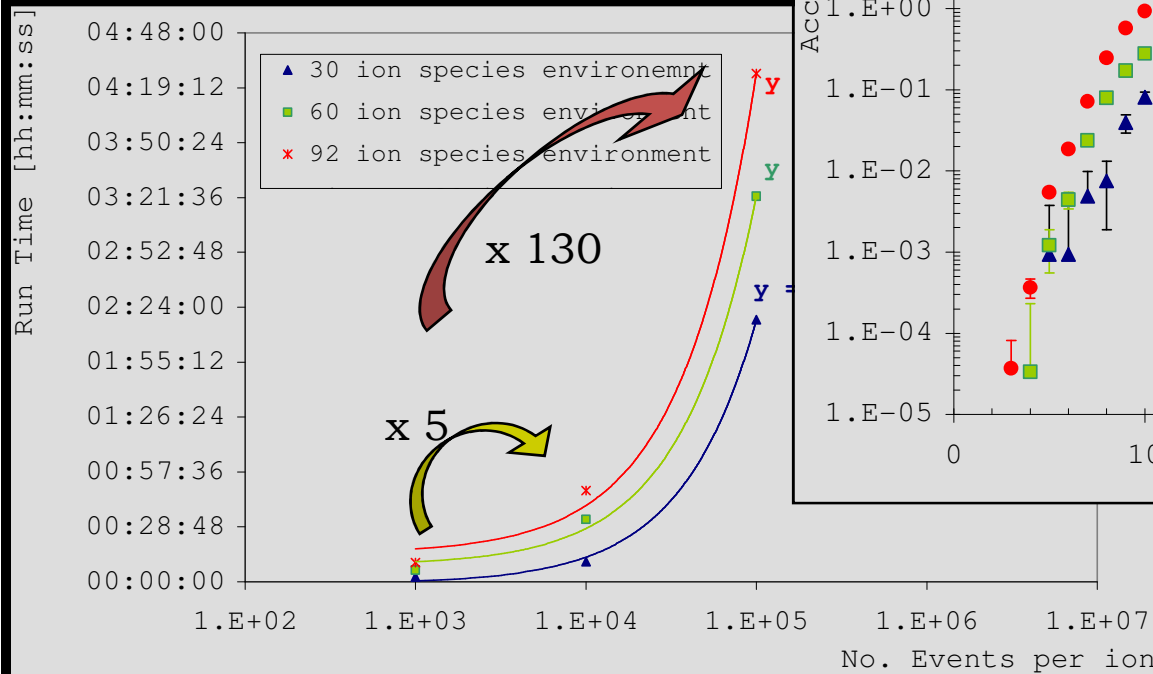
$$\text{Total Flux Norm.} = \text{PrimFlxuNorm} * \text{GeomAccept} * \text{SolidAnglNorm}$$

Full spectrum simulation

- CODES pre-processor takes inputs for several ions' energy spectra in SPENVIS format and others
- Computes individual contributions for SEE rates
- Outputs the total rate prediction



- The framework is working properly under :
 - Windows Internet Explorer
 - Google Chrome
 - Firefox

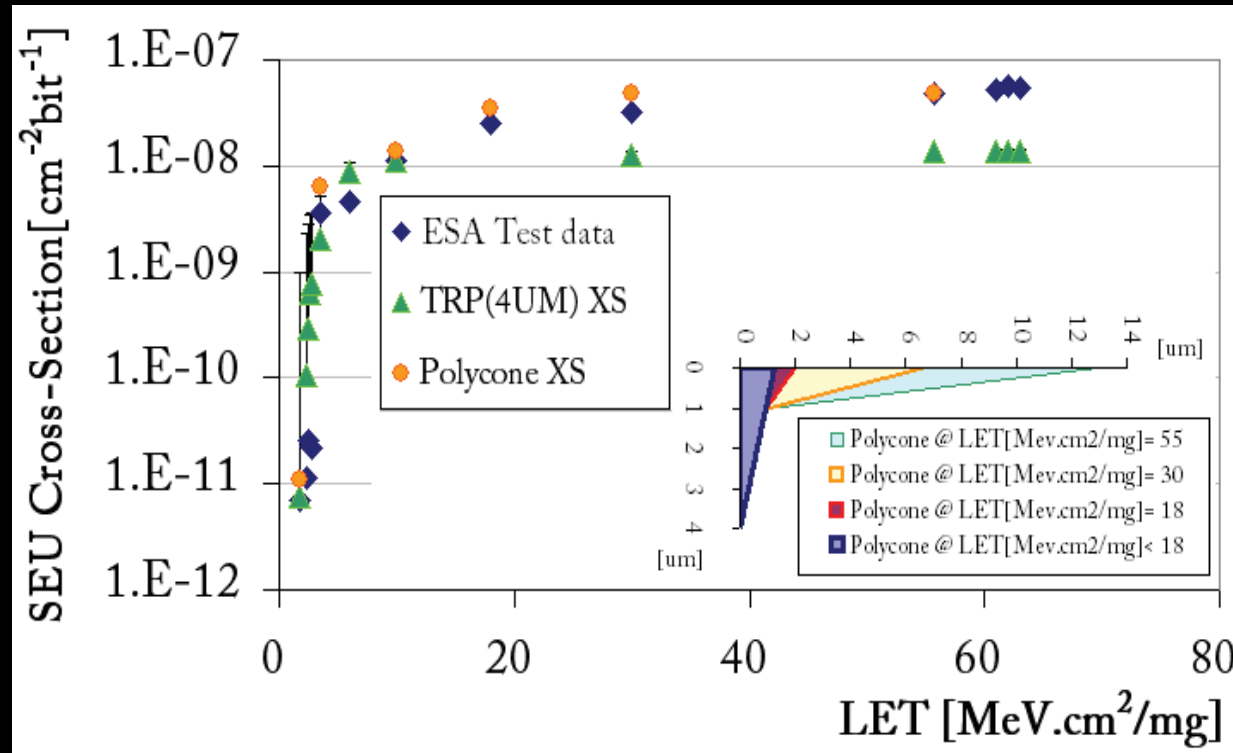


Additional models developed: that might be implemented

With SVFIT

Area increment above LET knee: Model & Results

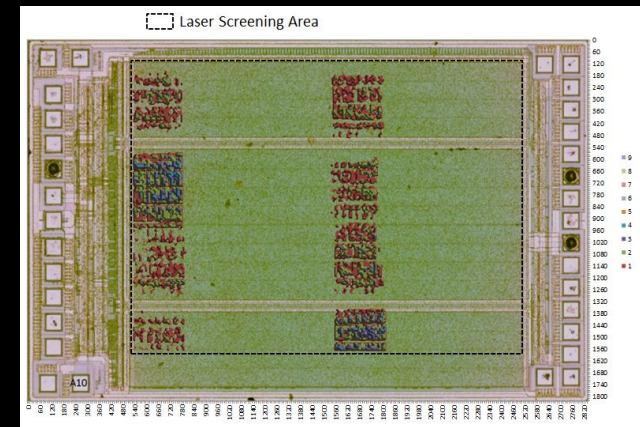
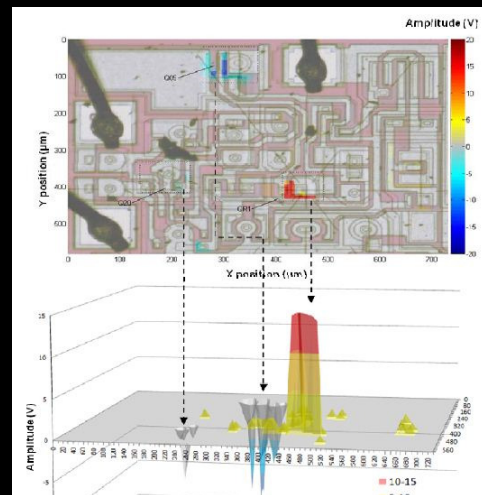
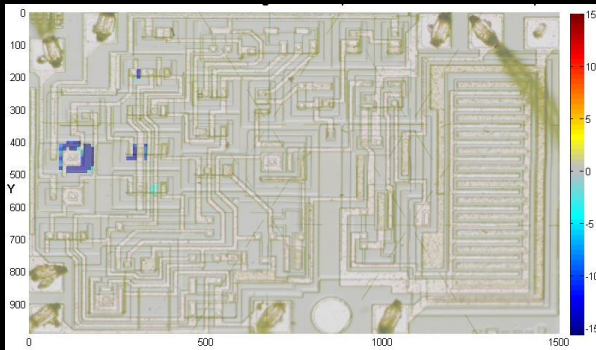
- Results published at RADECS 2011



- Doi:
[10.1109/RADECS.2011.6131414](https://doi.org/10.1109/RADECS.2011.6131414)

Efficiency matrix from Laser maps

- The model of defining a complex efficiency matrix was developed for SVFIT
- Objective : robust module for extraction from **laser maps** the charge **collection efficiency**
- SVFIT and CODES : benefit from the inclusion under the user-friendly interface



Images from of Isabel Lopez

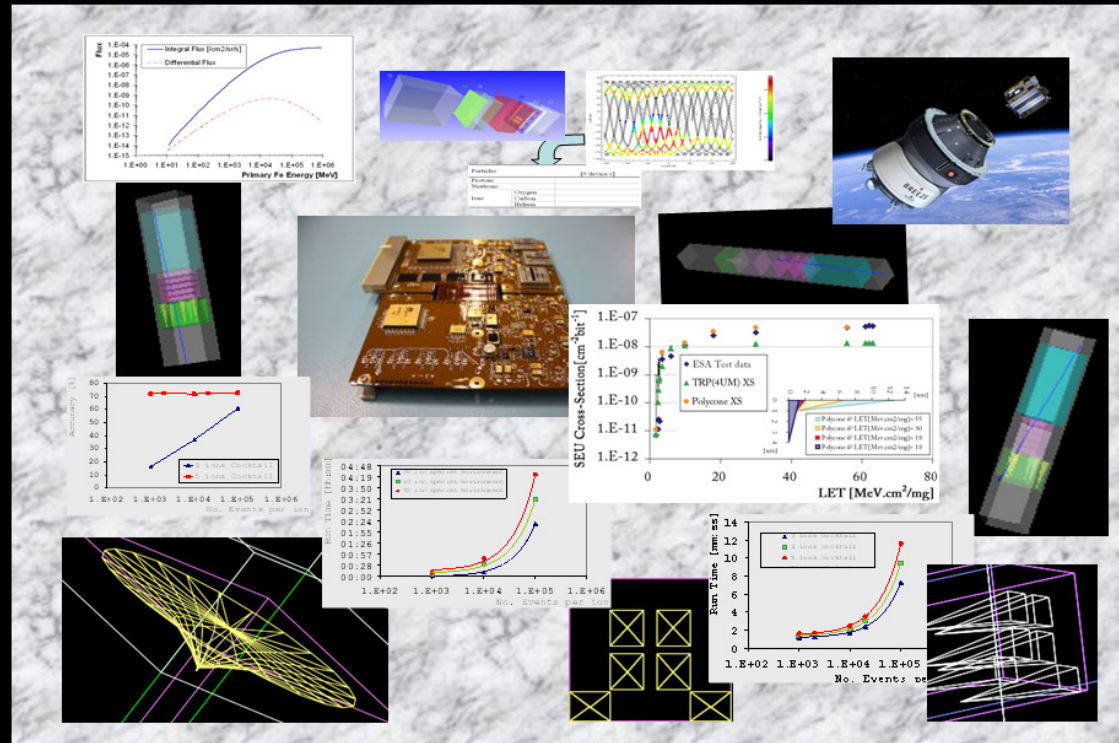
- CODES modules: top level user friendly tool, with a web-interface
- Tests show the robustness of the tool: consistency, accuracy & run time
- Results show :
 - Very good reconstruction of device response function (3-5 ion cocktails): excellent SVFIT
 - Accuracy statistics independent (5 ion cocktails)
 - Run time : SV shape fit : (3 to 5 ions) - 2 geometries : btw 2-10 min statistics
 - Run time : SV shape and depth fir: (5 ions) - 6 geometries : ~ 30 minutes
 - mCODES higher independence from user definitions: stand. statistical methods and sCODES

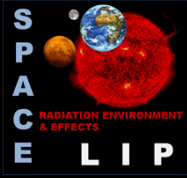
- Distribution of the tool
- Inclusion of ready-to-use developed models
- Incrementation of the Device Library
- Further models investigated: TRL needs to be increased

Thank you

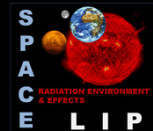
Component Degrade

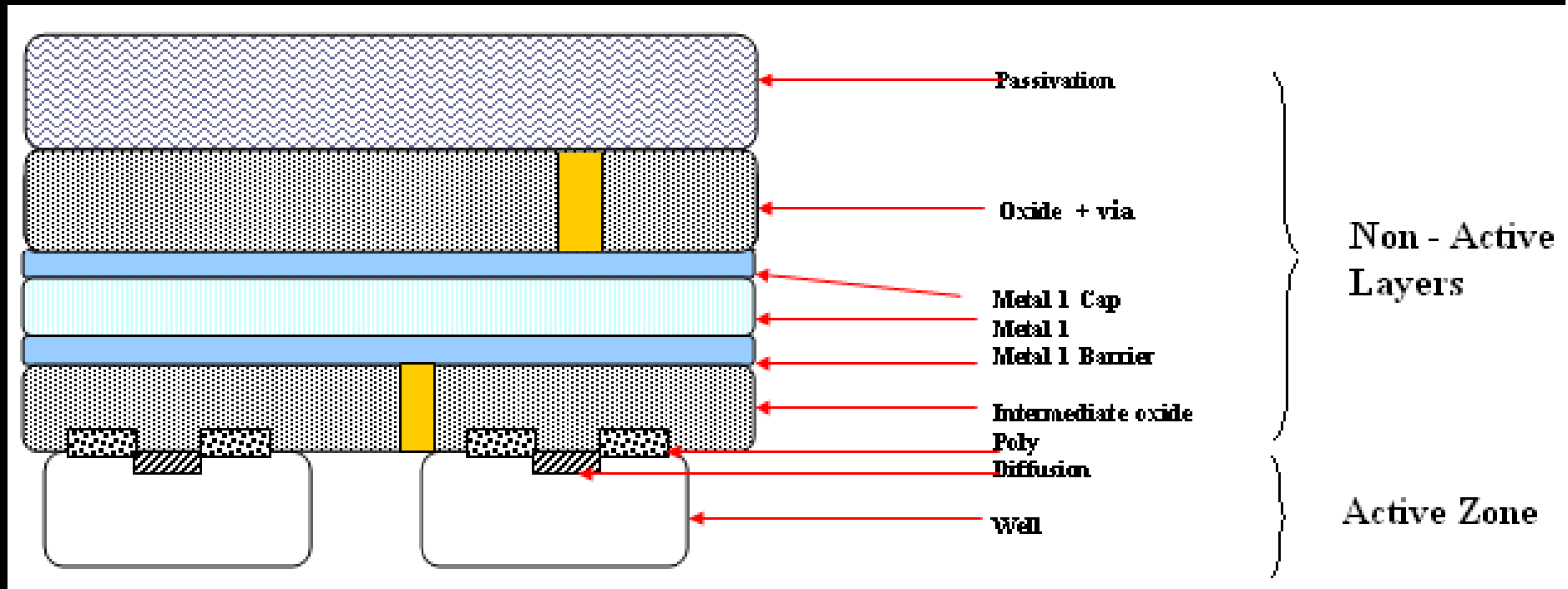
MODES





Additional slides





CODES Non-Active Layers - Google Chrome
www.cybercodes.net/framework/v1.5.9.7/WebInterface/codes/nonActiveLayersWin

Layer 1

Type of layer definitions:

Material:

Density[gr/cm3]:

Dimensions[um]: x y Depth

Layer position relative to SV:

Pos.x[um]:

Pos.y[um]:

Layer 2

Type of Packaging definitions:

Material:

Density[gr/cm3]:

Dimensions[um]: x y Depth

Layer position relative to SV:

Pos.x[um]:

Pos.y[um]:

CODES Non-Active Layers - Google Chrome
www.cybercodes.net/framework/v1.5.9.7/WebInterface/codes/nonActiveLayersWin

Layer 1

Type of layer definitions:

Material:

Density[gr/cm3]:

Dimensions[um]: x y Depth

Layer position relative to SV:

Pos.x[um]:

Pos.y[um]:

Layer 2

Type of Packaging definitions:

Material:

Density[gr/cm3]:

Dimensions[um]: x y Depth

Layer position relative to SV:

Pos.x[um]:

Pos.y[um]:

CODES Non-Active Layers - Google Chrome

www.cybercodes.net/framework/V1.5.9.7/WebInterface/codes/nonActiveLayersWin

Layer 1

Type of layer definitions: Metal

Material: Al

Density[gr/cm3]: 2.7

Dimensions[um]: x y Depth

Layer position relative to SV:

Pos.x[um]:

Pos.y[um]:

Layer 2

Type of Packaging definitions: Oxide/insulator/passivat

Material: SiO2

Density[gr/cm3]:

Dimensions[um]: x y Depth

Layer position relative to SV:

Pos.x[um]:

Pos.y[um]:

Update Data

CODES Non-Active Layers - Google Chrome

www.cybercodes.net/framework/V1.5.9.7/WebInterface/codes/nonActiveLayersWin

Layer 1

Type of layer definitions: Metal

Material: Al

Density[gr/cm3]: 2.7

Dimensions[um]: x y Depth

Layer position relative to SV:

Pos.x[um]:

Pos.y[um]:

Layer 2

Type of Packaging definitions: Via

Material: Ti

Density[gr/cm3]:

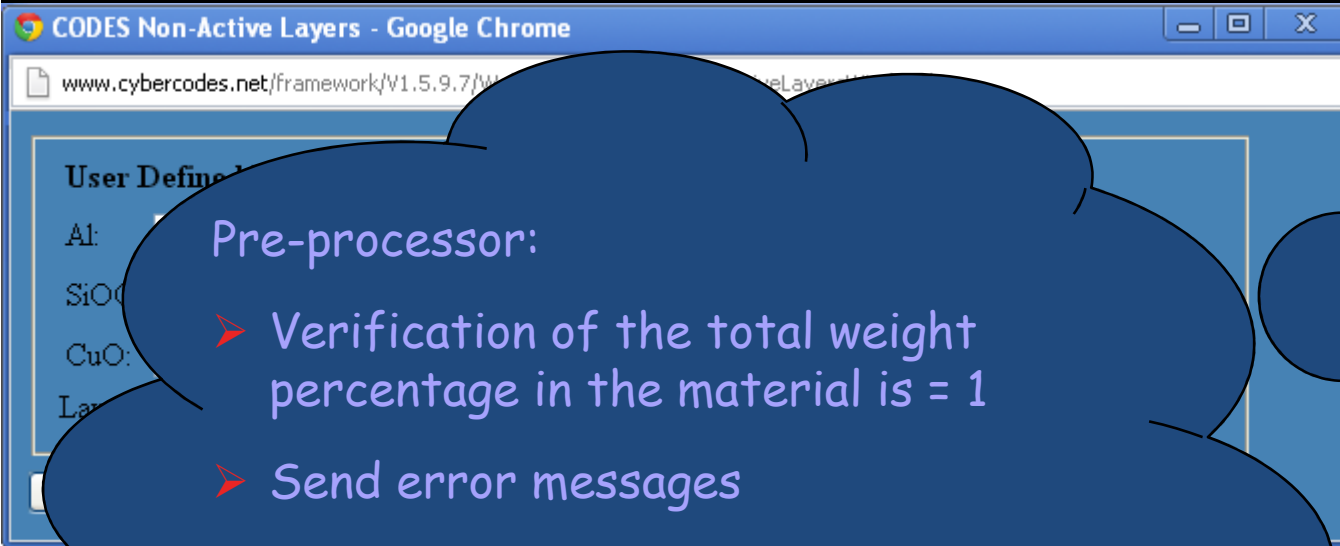
Dimensions[um]: x y Depth

Layer position relative to SV:

Pos.x[um]:

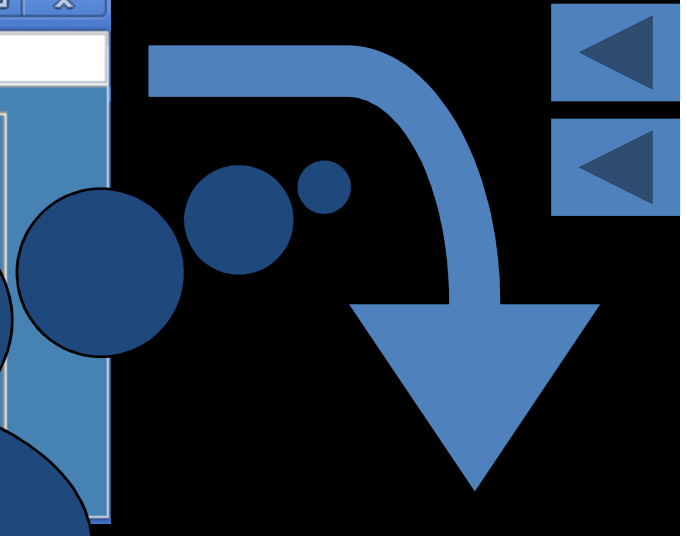
Pos.y[um]:

Update Data



Pre-processor:

- Verification of the total weight percentage in the material is = 1
- Send error messages
- Compute total density
- Compute layer positions in relation to device structure
- Write NALFile.txt with NAL table
- ✓ All have been verified



CYBERoffice
Software INFORMÁTICA E SERVIÇOS

CdO	MgO	Density [g/cm ³]	Dimension			Position		
			X [um]	Y [um]	Z [um]	XPos [um]	YPos [um]	ZPos [um]

LIP & CYBEROFFICE

SV Volume definition

Geometry

Aluminium Equivalent
Shielding Layer [mm]:

Non active layers: ▼

Sensitive volume: ▼

Regions in the memory cell: 1 2 4 6

Geometry: ▼

Dimensions[um]: X Y Depth

Geometry

Aluminium Equivalent
Shielding Layer [mm]:

Non active layers: ▼

Sensitive volume: ▼

No file chose

▼

Geometry

Aluminium Equivalent
Shielding Layer [mm]:

Non active layers: ▼

Sensitive volume: ▼

910138_FinalOutput.txt

Regions in the memory cell: 1 2 4 6

Geometry: ▼

Dimensions[um]: Depth

Geometry

Aluminium Equivalent
Shielding Layer [mm]:

Non active layers: ▼

Sensitive volume: ▼

910138_FinalOutput.txt

Regions in the memory cell: 1 2 4 6

Geometry: ▼

Dimensions[um]: x y Depth



Radiation Input

Load radiation input file:
 No file chosen

Particle:

Ion specific label:

Flux Units:

Energy	Flux
1.1295E+01	3.3381E-07
1.4219E+01	5.1410E-07
1.7901E+01	7.8358E-07

Radiation Input

Load radiation input file:
 No file chosen

Particle:

Ion specific label:

Flux Units:

Energy	Flux
1.1295E+01	3.3381E-07
1.4219E+01	5.1410E-07
1.7901E+01	7.8358E-07

Particle:

Ion specific label:

Flux Units:

Energy	Flux
1.1295E+01	3.3381E-07
1.4219E+01	5.1410E-07
1.7901E+01	7.8358E-07



Device Response Function

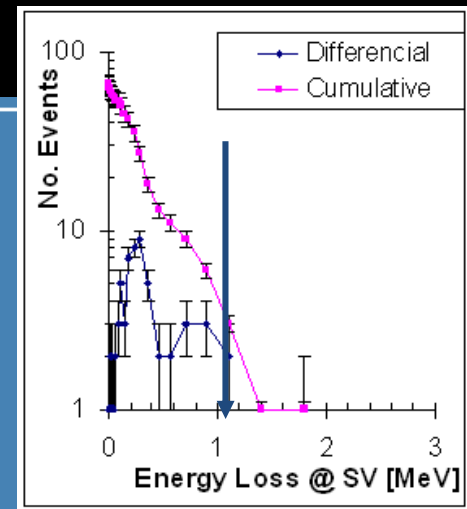
Device Response function

Select Method: No file chose

Device Response function

Select Method: 910138_FinalOutput.txt

Critical Energy [MeV]:



$$SEU = \text{No. Event} * \text{NormF}$$

Device Response function

Select Method:

Select Weibull Method:

Plateaux [cm2/bit]:

With Parameter [MeV]:

Exponent:

Threshold Energy [MeV]:

Device Response function

Select Method:

Select Weibull Method:

Plateaux [cm2/bit]:

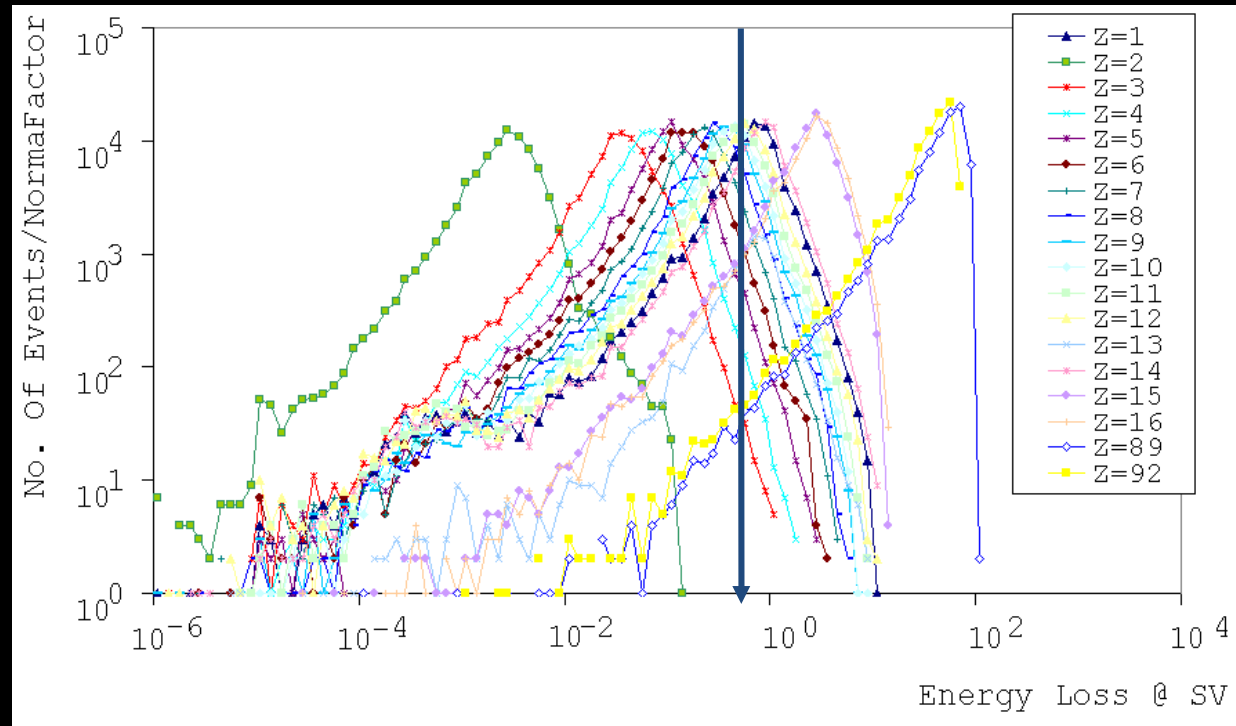
With Parameter [MeV*cm2/mg]:

Exponent:

Threshold Energy [MeV*cm2/mg]:

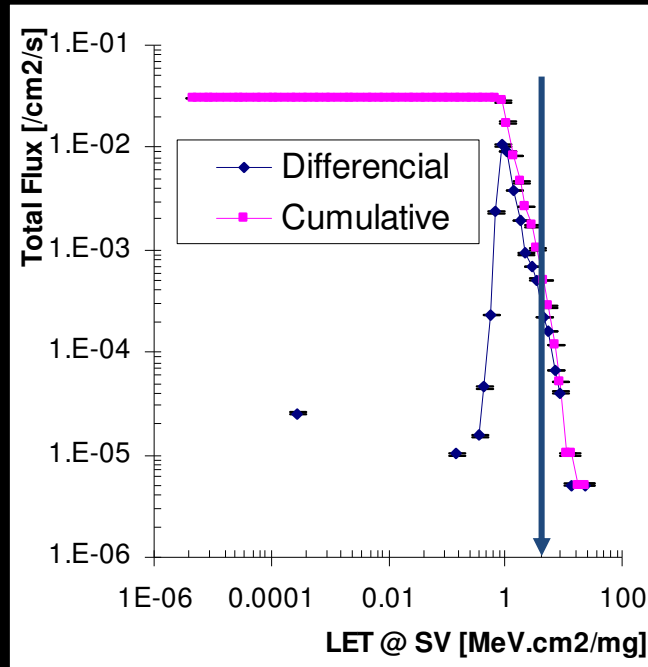
ID	Plateaux	With	Exp	Thres.
n	3.53E-14	4	1	10
p	3.53E-14	4	1	10
hi	1.50E-07	65	1.4 7	1.2

SEU calculation with mCODES



$$\text{SEU Rate} = \text{No Evts (Edep} > \text{Ec)} / \text{NGen} * \text{Total Flux} * \text{Active Area}$$

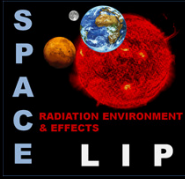
SEU calculation with sCODES



ID	Plateaux	With	Exp	Thres.
n	3.53E-14	4	1	10
p	3.53E-14	4	1	10
hi	1.50E-07	65	1.47	2



$$\text{SEU Rate} = \text{No Evts (LET} > \text{Th)} / \text{NGen} * \text{Total Flux} * \langle \text{SEU_XS} \rangle$$



SVFIT automatic/iterative

- Modular iterative tool
- Microdosimetry Monte-Carlo
- Device sensitive volume: cha collection.
- Input parameters:
 - Ion cocktails description
 - Irradiation test data
- SEU threshold definition
- SV shape modulation
- Output:
 - best SV shape to fit ion test
 - Threshold Energy loss for S
 - Reconstructed SEE XS curv

Results

```
SVFIT interactive mode final results
Best geometry description
User input data:
For (6) SV volumes
SVx 1 um
SVy 0.81 um
SVz 3 um Depth +/- 10%                                uncertainty

Best geometry shape: TRP
Accuracy: 74.3131

*****;
Cross section detail for different geometries;
*****;
SVdepth  SVz      3 um

*****;
LET;SEE XS (exp);SEEXS (rpp);SEEXS (trp);
*****;
1.7;6.9700E-12;1.652400000000000020821e-09 ;2.235600000000000042767e-09 ;
3.5;3.64262E-9;0 ;7.3872000000000000112547e-09 ;
6;4.63064E-9;1.5066000000000000007063e-08 ;1.049760000000000006416e-08 ;
10;1.12421E-8;1.53576000000000000024704e-08 ;1.2150000000000000012634e-08 ;
30;3.27837E-8;1.48716000000000000022875e-08 ;1.4191200000000000020315e-08 ;
*****;
Best geometry: TRP;Accuracy: 72.7144%;

SVdepth  SVz+10% uncertainty3.3 um
*****;
LET;SEE XS (exp);SEEXS (rpp);SEEXS (trp);
*****;
1.7;6.9700E-12;1.06920000000000000007147e-08 ;2.5272000000000000012381e-09 ;
3.5;3.64262E-9;1.574640000000000000026167e-08 ;7.3872000000000000112547e-09 ;
6;4.63064E-9;1.526040000000000000007795e-08 ;1.06920000000000000007147e-08 ;
10;1.12421E-8;1.516320000000000000023972e-08 ;1.1858400000000000011536e-08 ;
30;3.27837E-8;0 ;1.555200000000000000025436e-08 ;
*****;
Best geometry: TRP;Accuracy: 74.3131%;

SVdepth  SVz-10% uncertainty2.7 um
*****;
LET;SEE XS (exp);SEEXS (rpp);SEEXS (trp);
*****;
1.7;6.9700E-12;1.341360000000000000017389e-08 ;1.5552000000000000017164e-09 ;
3.5;3.64262E-9;0 ;6.512400000000000000079628e-09 ;
6;4.63064E-9;1.302480000000000000015926e-08 ;1.0303200000000000005684e-08 ;
10;1.12421E-8;0 ;1.108080000000000000000861e-08 ;
30;3.27837E-8;1.36080000000000000001812e-08 ;1.3996800000000000019583e-08 ;
*****;
Best geometry: TRP; Accuracy: 72.8557%;
```

